AMENDMENTS TO THE CLAIMS

Please replace the claims with the following rewritten listing:

1. (Currently Amended) A wiring structure of a semiconductor device, comprising:

a body formed of a first conductive material in a first insulating film on a semiconductor substrate; and

a protrusion formed of a second conductive material in a second insulating film formed on the first insulating film, the protrusion being connected to an upper surface of the body and formed to have a width less than a width of the body, and including a planarized upper surface;

wherein the semiconductor device is an SRAM device and the wiring is a v_{ss} line or a word line.

2. (Original) The wiring structure of claim 1, wherein the body has a shape of a polygonal column.

3. (Original) The wiring structure of claim 1, wherein the body has a shape of a hemispherical column.

4. (Original) The wiring structure of claim 1, wherein the first conductive material is one selected from a group consisting of tungsten, aluminum, tungsten alloy, and aluminum alloy.

5. (Original) The wiring structure of claim 1, wherein the second conductive material is one selected from a group consisting of tungsten, aluminum, tungsten alloy, and aluminum alloy.

6. (Canceled)

7. (Original) The wiring structure of claim 1, wherein the first insulating film is formed of a material having an etching rate greater than that of the second insulating film.

8. (Original) The wiring structure of claim 1, further comprising a conductive stud insulated from the wiring by the first insulating film and the second insulating film, connected to the semiconductor substrate, and having a planarized surface having the same height as the planarized surface of the wiring.

9. (New) A wiring structure of a semiconductor device, comprising:

a body formed of a first conductive material in a first insulating film on a semiconductor substrate;

a protrusion formed of a second conductive material in a second insulating film formed on the first insulating film, the protrusion being connected to an upper surface of the body and formed to have a width less than a width of the body, and including a planarized upper surface; and

a conductive stud insulated from the wiring by the first insulating film and the second insulating film, connected to the semiconductor substrate, and having a planarized surface having the same height as the planarized surface of the wiring.

10. (New) The wiring structure of claim 9, wherein the body has a shape of a polygonal column.

11. (New) The wiring structure of claim 9, wherein the body has a shape of a hemispherical column.

12. (New) The wiring structure of claim 9, wherein the first conductive material is one selected from a group consisting of tungsten, aluminum, tungsten alloy, and aluminum alloy.

13. (New) The wiring structure of claim 9, wherein the second conductive material is one selected from a group consisting of tungsten, aluminum, tungsten alloy, and aluminum alloy.

14. (New) The wiring structure of claim 9, wherein the semiconductor device is an SRAM device and the wiring is a v_{SS} line or a word line.

15. (New) The wiring structure of claim 9, wherein the first insulating film is formed of a material having an etching rate greater than that of the second insulating film.